DATA SHEET

SILICON POWER TRANSISTOR 2SA1129

PNP SILICON EPITAXIAL TRANSISTOR FOR LOW-FREQUENCY POWER AMPLIFIERS AND MID-SPEED SWITCHING

The 2SA1129 is a mold power transistor developed for mid-speed switching, and is ideal for use as a ramp driver.

ORDERING INFORMATION

Part No.	Package
2SA1129	TO-220AB

(TO-220AB)

FEATURES

NEC

- Large current capacity with small package: Ic(DC) = -7.0 A
- · Low collector saturation voltage: VCE(sat) = -0.3 V MAX. @Ic = -3.0 A, IB = -0.1 A
- · Complementary transistor: 2SC2654

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Parameter	Symbol	Conditions	Ratings	Un <mark>it</mark>
Collector to base voltage	Vсво		-30	V
Collector to emitter voltage	VCEO		-30	V
Emitter to base voltage	Vево		-7.0	V
Collector current (DC)	IC(DC)		-7.0	Α
Collector current (pulse)	C(pulse)	PW ≤ 300 <i>µ</i> s,	-15	Α
		duty cycle ≤ 10%		
Base current (DC)	B(DC)		-3.5	А
Total power dissipation	Рт	Tc = 25°C	40	W
		$T_A = 25^{\circ}C$	1.5	W
Junction temperature	Tj		150	°C
Storage temperature	Tstg		-55 to +150	°C

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Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = -30 \text{ V}, \text{ I}_{E} = 0 \text{ A}$			-10	μA
Emitter cutoff current	Іево	V _{EB} = -5.0 V, Ic = 0 A			-10	μA
DC current gain	hfe1	$V_{CE} = -1.0 \text{ V}, \text{ Ic} = -3.0 \text{ A}^{Note}$	40		200	
DC current gain	hFE2	$V_{CE} = -1.0 \text{ V}, \text{ Ic} = -5.0 \text{ A}^{Note}$	20			
Collector saturation voltage	VCE(sat)1	$I_{C} = -3.0 \text{ A}, I_{B} = -0.1 \text{ A}^{Note}$			-0.3	V
Collector saturation voltage	VCE(sat)2	$I_{C} = -5.0 \text{ A}, I_{B} = -0.5 \text{ A}^{Note}$			-0.6	V
Base saturation voltage	VBE(sat)1	$I_{C} = -3.0 \text{ A}, I_{B} = -0.1 \text{ A}^{Note}$			-1.5	V
Base saturation voltage	VBE(sat)2	$I_{C} = -5.0 \text{ A}, I_{B} = -0.5 \text{ A}^{Note}$			-2.0	V
Turn-on time	ton	Ic = -5.0 A, R _L = 4.0 Ω,			1.0	μs
Storage time	tstg	$I_{B1} = -I_{B2} = -0.5 \text{ A}, \text{ Vcc} \cong -20 \text{ V}$			2.5	μs
Fall time	tr	PW = 50 μ s, duty cycle = 2%			1.0	μs

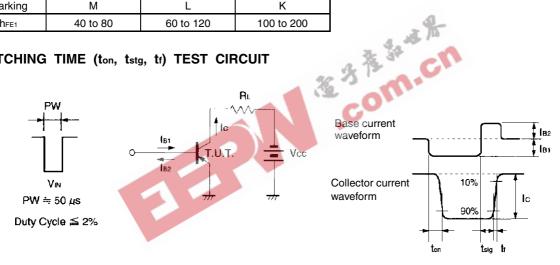
ELECTRICAL CHARACTERISTICS (TA = 25°C)

Note Pulse test PW \leq 350 μ s, duty cycle \leq 2%

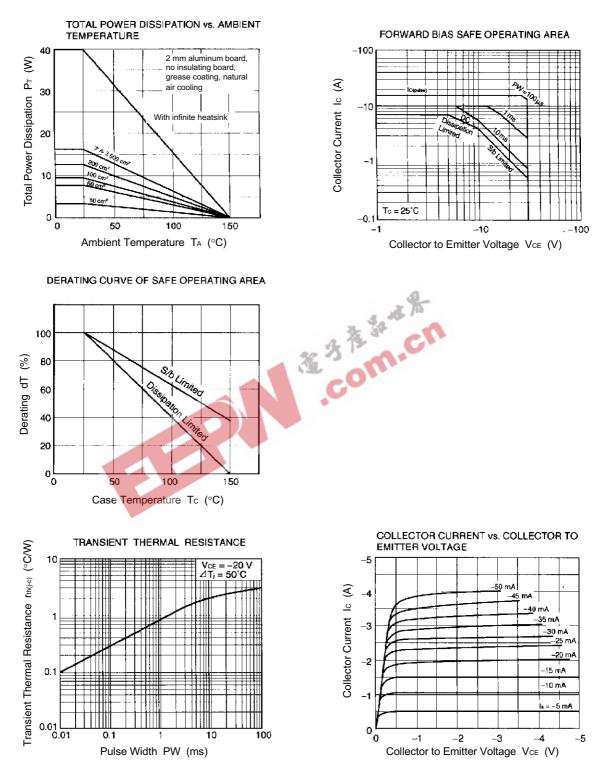
hfe CLASSIFICATION

Marking	М	L	К	
hfe1	40 to 80	60 to 120	100 to 200	

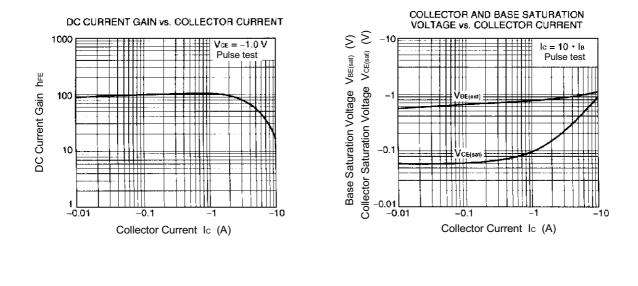
SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT







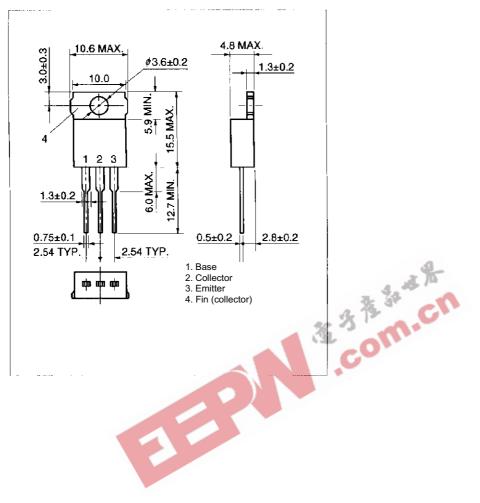
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PACKAGE DRAWING (UNIT: mm)

TO-220AB (MP-25)



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